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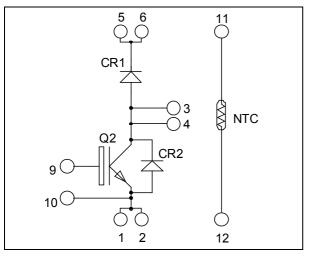
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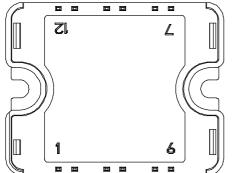
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Boost chopper Trench + Field Stop IGBT3 Power Module





Pins 1/2; 3/4; 5/6 must be shorted together

Absolute maximum ratings

Symbol Parameter Max ratings Unit Collector - Emitter Breakdown Voltage 1700 V_{CES} V $T_C = 25^{\circ}C$ 45 Continuous Collector Current I_C $T_{\rm C} = 80^{\circ}{\rm C}$ 30 Α Pulsed Collector Current $T_C = 25^{\circ}C$ 70 I_{CM} Gate - Emitter Voltage V V_{GE} ± 20 $T_C = 25^{\circ}C$ W P_{D} Maximum Power Dissipation 210 RBSOA Reverse Bias Safe Operating Area $T_i = 125^{\circ}C$ 60A@1600V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

$V_{CES} = 1700V$ $I_{C} = 30A$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics								
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				250	μΑ	
V _{CE(sat)}	Collector Emitter saturation Voltage		$T_j = 25^{\circ}C$		2.0	2.4	V	
V CE(sat)	Concetor Enniter saturation voltage	$I_C = 30A$	$T_{j} = 125^{\circ}C$		2.4		v	
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1.5 \text{mA}$		5.2	5.8	6.4	V	
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$			2500		pF
Cres	Reverse Transfer Capacitance	f = 1 MHz			90		pr
T _{d(on)}	Turn-on Delay Time	Inductive Switchin	ng (25°C)		100		
T _r	Rise Time	$V_{GE} = \pm 15V$			70		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 900V$ $I_{C} = 30A$			650		ns
T_{f}	Fall Time	$R_G = 18\Omega$		80			
T _{d(on)}	Turn-on Delay Time	Inductive Switchin		100			
Tr	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 30A$ $R_G = 18\Omega$			70		
T _{d(off)}	Turn-off Delay Time				750		ns
$T_{\rm f}$	Fall Time				100		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 900V$	$T_j = 125^{\circ}C$		17		I
E _{off}	Turn-off Switching Energy	$I_{C} = 30A$ $R_{G} = 18\Omega$	$T_j = 125^{\circ}C$		15		mJ

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1700			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1700V	$T_i = 25^{\circ}C$ $T_i = 125^{\circ}C$			250 500	μA
I _F	DC Forward Current		$T_{\rm C} = 80^{\circ}{\rm C}$		50	200	А
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 50 A$ $V_{\rm GE} = 0 V$	$T_j = 25^{\circ}C$		1.8	2.2	V
• F	Diode Forward Voltage		$T_{i} = 125^{\circ}C$		1.9		v
+	Deverse Deservery Time		$T_j = 25^{\circ}C$		385		20
t _{rr}	Reverse Recovery Time		$T_{j} = 125^{\circ}C$		490		ns
0		$I_F = 50A$	$T_j = 25^{\circ}C$		14		0
Q _{rr}	Reverse Recovery Charge	$V_R = 900V$ di/dt =800A/µs	$T_j = 125^{\circ}C$		23		μC
Б	Reverse Recovery Energy		$T_j = 25^{\circ}C$		6		mI
Er			$T_{j} = 125^{\circ}C$		12		mJ



Thermal and package characteristics

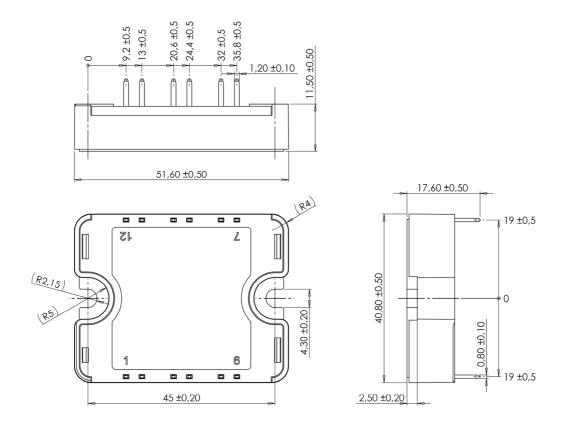
Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.60	°C/W
			Diode			0.70	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature	-40		100			
Torque	Mounting torque	To heatsink	x M4	2		3	N.m
Wt	Package Weight				80	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		Κ

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP1 Package outline (dimensions in mm)



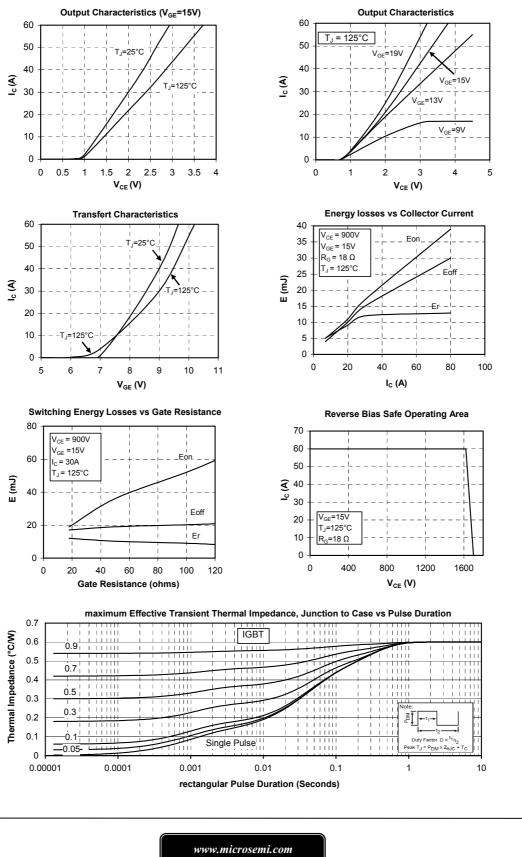
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

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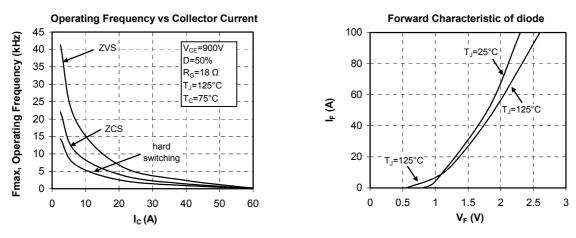
Typical Performance Curve

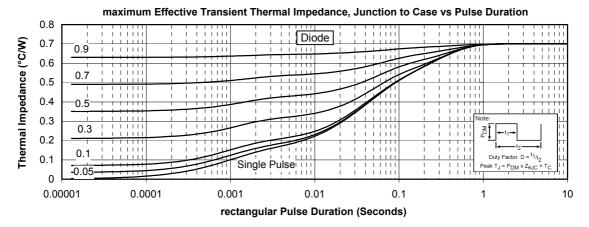


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